

**INDUSTRY STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

SJ/T 11973-2025

**Family specification for insulated gate bipolar transistors
(IGBT) modules used of renewable energy vehicle applications
(English Translation)**

Issued on: May 9, 2025

Implemented on: August 1, 2025

Issued by: Ministry of Industry and Information Technology

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What this standard covers

This standard specifies the model, dimensions, ratings, device characteristics, inspection rules, marking, and ordering requirements for Insulated Gate Bipolar Transistor (IGBT) modules used in new energy vehicles. This specification applies to IGBT modules used in new energy vehicles (including pure electric, hybrid, and fuel cell vehicles), covering circuit topologies such as single-transistor, half-bridge, and three-phase bridge circuits. Other similar IGBT module products can refer to this standard.

Document data

Estimated length of the Chinese original: 18,165 words.